



Shantou Huashan Electronic Devices Co.,Ltd.

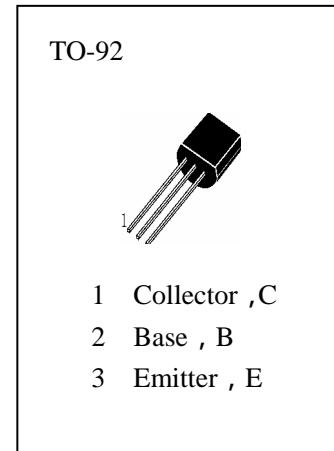
NPN SILICON TRANSISTOR

H548

SWITCHING AND AMPLIFIER

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$)

T_{stg} —Storage Temperature.....	-55~150
T_j —Junction Temperature.....	150
P_C —Collector Dissipation.....	500mW
V_{CBO} —Collector-Base Voltage.....	30V
V_{CEO} —Collector-Emitter Voltage.....	35V
V_{EBO} —Emitter-Base Voltage.....	5V
I_C —Collector Current.....	100mA



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	30			V	$I_C=100 \mu A, I_E=0$
BVCEO	Collector-Emitter Breakdown Voltage	30			V	$I_C=1mA, I_B=0$
BVEBO	Emitter-Base Breakdown Voltage	5			V	$I_E=1mA, I_C=0$
ICBO	Collector Cut-off Current			15	nA	$V_{CB}=30V, I_E=0$
HFE	DC Current Gain	110		800		$V_{CE}=5V, I_C=2mA$
VCE(sat1)	Collector- Emitter Saturation Voltage		90	250	mV	$I_C=10mA, I_B=0.5mA$
VCE(sat2)			200	600	mV	$I_C=100mA, I_B=5mA$
VBE(sat1)	Base-Emitter Saturation Voltage		0.7	1	V	$I_C=10mA, I_B=0.5mA$
VBE(sat2)			0.9	1.2	V	$I_C=100mA, I_B=5mA$
VBE(ON1)	Base-Emitter On Voltage	580	660	700	mV	$V_{CE}=5V, I_C=2mA$
f _T	Current Gain-Bandwidth Product		300		MHz	$V_{CE}=5V, I_C=10mA$
C _{ob}	Output Capacitance		2.5		pF	$V_{CB}=10V, I_E=0$ $f=100MHz$
NF	Noise Figure		2	10	dB	$V_{CE}=5V, I_C=200 \mu A$ $f=1KHz, R_g=2K$

h_{FE} Classification

A

B

C

110—220

200—450

420—800



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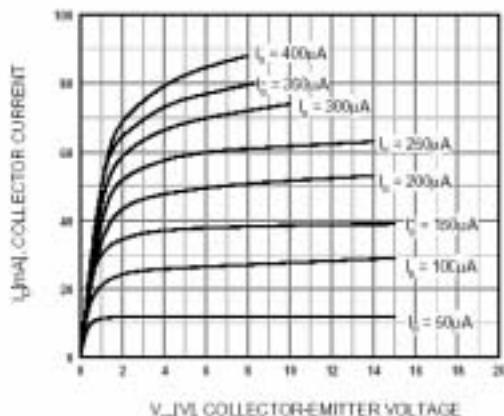


Figure 1. Static Characteristic

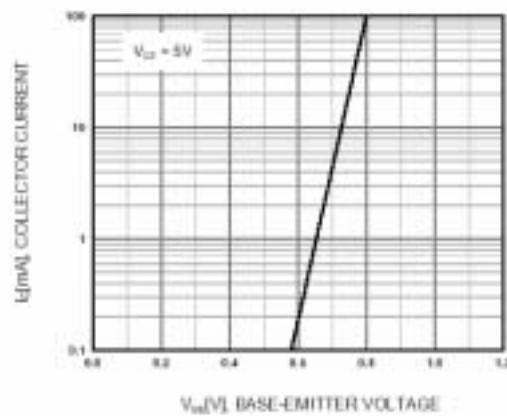


Figure 2. Transfer Characteristic

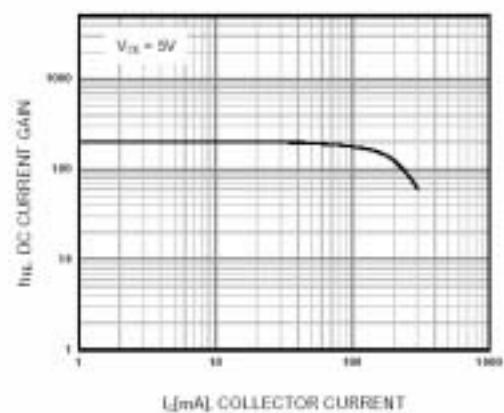


Figure 3. DC current Gain

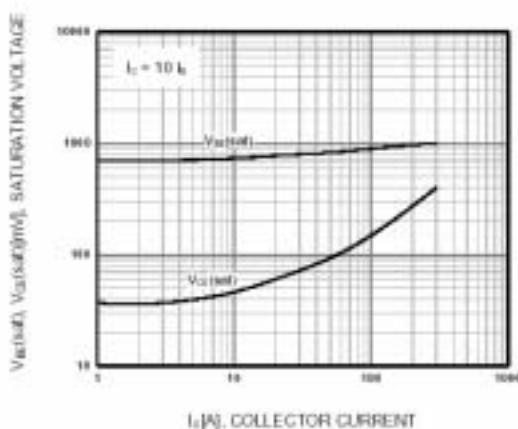


Figure 4. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

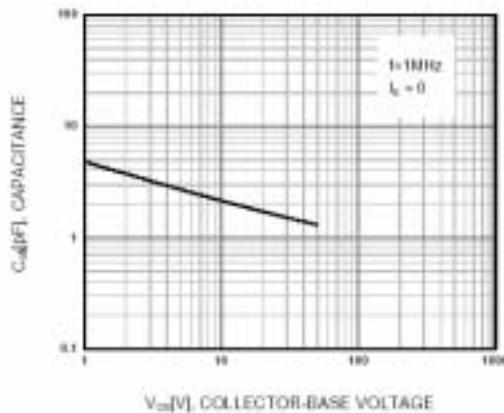


Figure 5. Output Capacitance

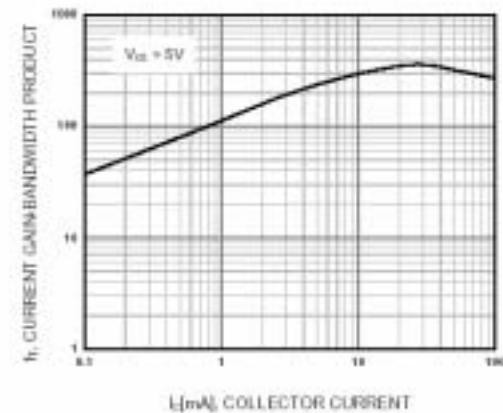


Figure 6. Current Gain Bandwidth Product